IFW

S/N 1<u>0</u>/796,514

**PATENT** 

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

pplicant:

John P. Snyder et al.

Examiner:

Su C. Kim

Serial No.:

10/796,514 Conf. No.: 1961

Group Art Unit: 2823

Filed:

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Attry. Dkt. No.: 14467.05

Title:

TRANSISTOR HAVING HIGH DIELECETRIC CONSTANT GATE

INSULATING LAYER AND SOURCE AND DRAIN FORMING

SCHOTTKY CONTACT WITH SUBSTRATE

## TRANSMITTAL FOR AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

We are transmitting herewith the following attached items (as indicated with an "X"):

X This Transmittal and a Return Postcard;

X An Amendment and Response under 37 CFR § 1.111 (20 pages);

SPINNAKER SEMICONDUCTOR, INC 3769 WESCOTT HILLS DRIVE

EAGAN, MN 55123

NAME: DAVID J. KING

REG. No. 53,132

<u>CERTIFICATE OF MAILING UNDER 37 CFR 1.8:</u> I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Mail Stop Amendment, Commissioner of Patents, P.O. Box 1450, Washington, D.C. 22313-1450, on the 7<sup>th</sup> day of April, 2008.

y: David I King Reg No. 53 1